

## Silicon NPN Power Transistors

## 2SC4927

## DESCRIPTION

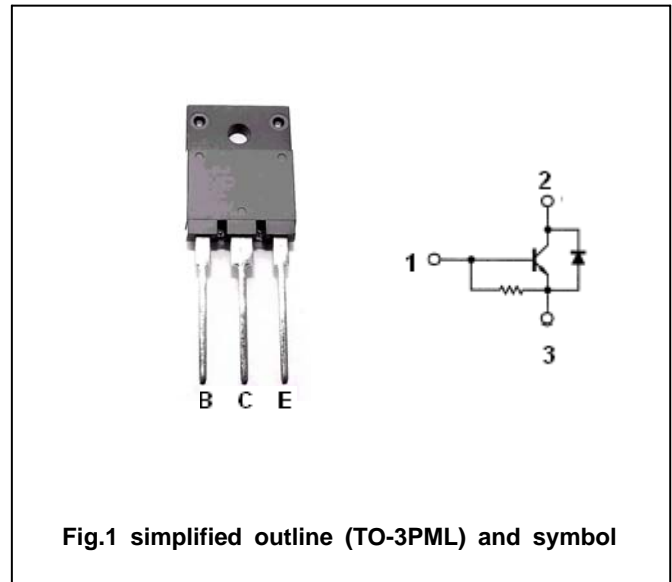
- With TO-3PML package
- Built-in damper diode
- High breakdown voltage

## APPLICATIONS

- TV/Character display horizontal deflection output applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings( $T_a=25^{\circ}\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CEO}$	Collector-emitter voltage	Open base	1500	V
$V_{EBO}$	Emitter-base voltage	Open collector	6	V
$I_C$	Collector current		8	A
$I_{C(\text{peak})}$	Collector current-peak		9	A
$I_{C(\text{surge})}$	Collector current-surge		18	A
$I_o$	C to E diode forward current		8	A
$P_C$	Collector power dissipation	$T_C=25^{\circ}\text{C}$	50	W
$T_j$	Junction temperature		150	$^{\circ}\text{C}$
$T_{\text{stg}}$	Storage temperature		-55~150	$^{\circ}\text{C}$

## Silicon NPN Power Transistors

## 2SC4927

## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =500mA ; I <sub>C</sub> =0	6			V
I <sub>CES</sub>	Collector cut-off current	V <sub>CE</sub> =1500V; R <sub>BE</sub> =0			0.5	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V			25	
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =6A ; I <sub>B</sub> =1.2A			5	V
V <sub>BE(sat)</sub>	Base-emitter saturation voltage	I <sub>C</sub> =6A ; I <sub>B</sub> =1.2A			1.5	V
V <sub>ECF</sub>	Diode forward voltage	I <sub>F</sub> =8A			2.0	V
t <sub>f</sub>	Fall time	I <sub>CP</sub> =6A; f <sub>H</sub> =31.5kHz I <sub>B1</sub> =1.2A; I <sub>B2</sub> =-2.4A			0.5	μ s

Silicon NPN Power Transistors

2SC4927

PACKAGE OUTLINE

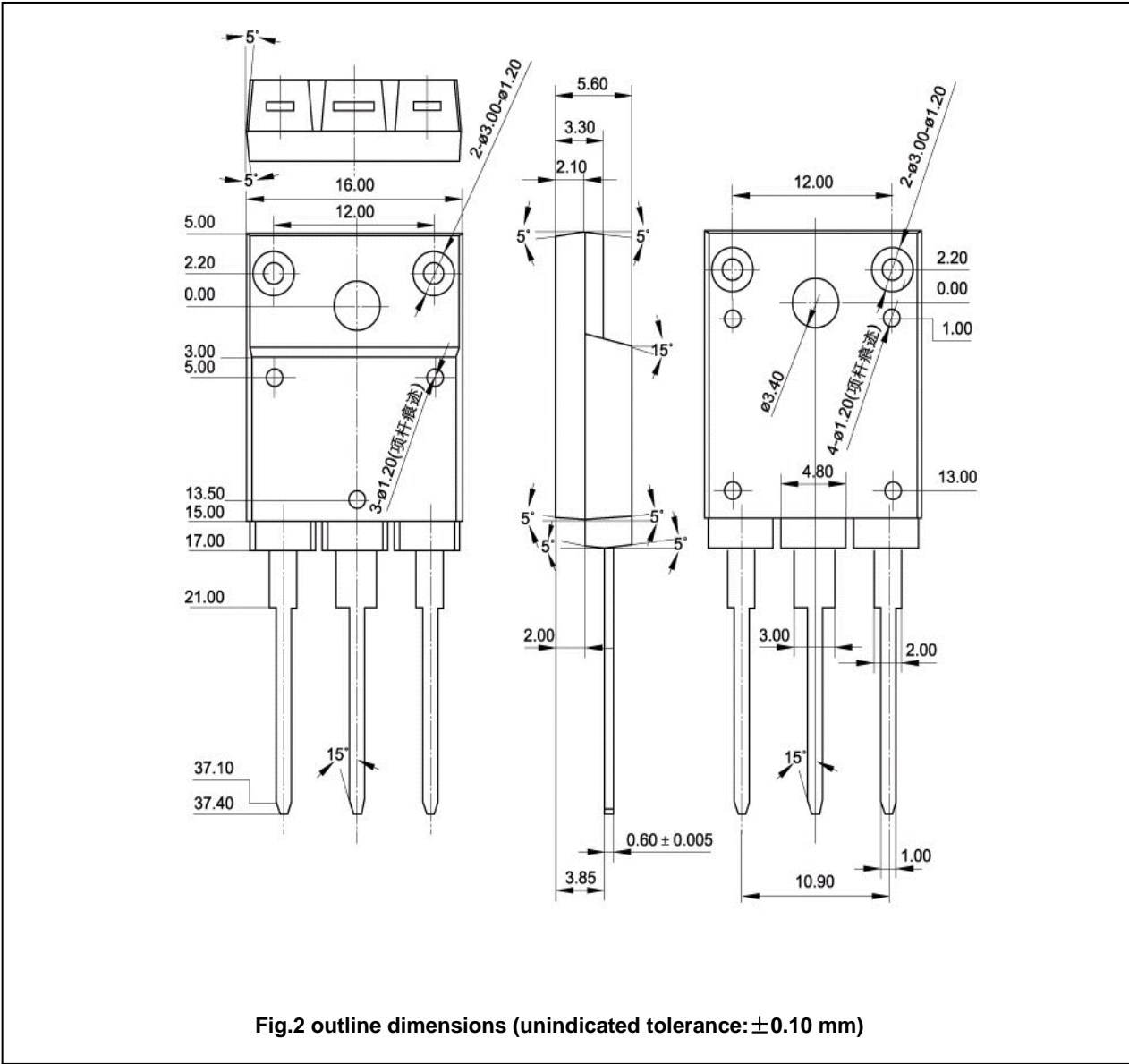


Fig.2 outline dimensions (unindicated tolerance:  $\pm 0.10$  mm)

## Silicon NPN Power Transistors

2SC4927

